Unit in mm

TOSHIBA DIODE SILICON EPITAXIAL PLANAR TYPE

1 S S 2 5 0

HIGH SPEED SWITCHING APPLICATIONS.

• Low Forward Voltage : V_F(2)=0.90V (Typ.)

• Fast Reverse Recovery Time: trr=60ns (Max.)

• Small Total Capacitance : C_T=1.5pF (Typ.)

• Small Package : SC-59

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Peak Reverse Voltage	V_{RM}	250	V	
Reverse Voltage	$V_{\mathbf{R}}$	200	V	
Peak Forward Current	I_{FM}	300	mA	
Average Forward Current	IO	100	mA	
Surge Current (10ms)	I_{FSM}	2	Α	
Power Dissipation	P	150	mW	
Junction Temperature	Tj	125	°C	
Storage Temperature Range	$T_{ m stg}$	-55~125	°C	

1. ANODE 2. N.C.

S-MINI 3. CATHODE

JEDEC TO-236MOD

EIAJ SC-59

TOSHIBA 1-3G1B

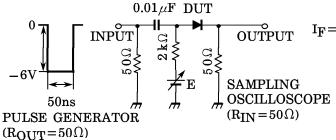
Weight: 0.012g

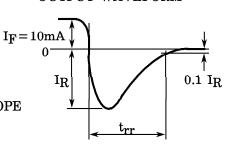
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

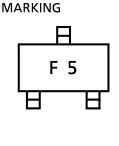
EEECTION E CITATORETER	1511C5 (14 -	- 25 4)	0	0		
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V _{F (1)}	I _F =10mA	_	0.72	1.00	V
	$V_{F(2)}$	$I_{\mathbf{F}} = 100 \text{mA}$	_	0.90	1.20	
neverse Current	$I_{R(1)}$	$V_R = 50V$	_	_	0.1	μ A
	$I_{R(2)}$	V_R =200 V	_	_	1.0	
Total Capacitance	C_{T}	$V_R=0$, f=1MHz	_	1.5	3.0	рF
Reverse Recovery Time	t _{rr}	I _F =10mA (Fig.1)	_	10	60	ns

Fig1. REVERSE RECOVERY TIME (trr) TEST CIRCUIT

INPUT WAVEFORM OUTPUT WAVEFORM

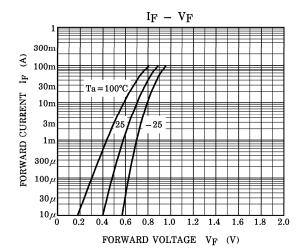


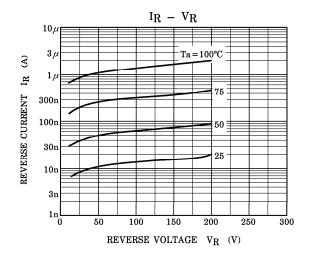


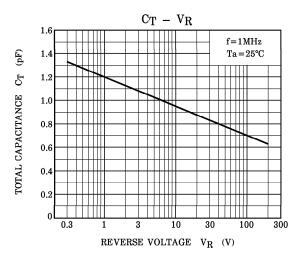


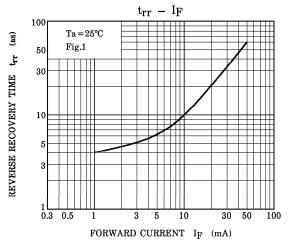
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